WHAT IS CLAIMED IS:

1. A composition comprising:

a) an abrasive;

b) a first surfactant comprising a phosphate;

c) a second surfactant comprising an acetylenic compound;

d) a complexing agent;

e) at least one azole; and

f) water

wherein the composition is free of poly(vinylpyrrolidone).

2. The composition of claim 1 wherein the abrasive is selected from the group consisting of alumina, fumed silica, colloidal silica, coated particles, titania, ceria, zirconia, and any combinations thereof.

3. The composition of claim 1 wherein the phosphate is selected from polyoxyethylene alkyl ether phosphates.

4. The composition of claim 1 wherein the phosphate is selected from polyoxyethylene aryl alkyl ether phosphates.

5. The composition of claim 1 wherein the phosphate is selected from polyoxyethylene nonylaryl ether phosphates.

6. The composition of claim 1 wherein the phosphate is selected from polyoxyethylene nonylphenyl ether phosphates.

7. The composition of claim 1 wherein the acetylenic compound is an acetylene glycol or an ethoxylated adduct thereof.

8. The composition of claim 1 wherein the acetylenic compound is an ethoxylated adduct of 2,4,7,9-tetramethyl-5-decyne-4,7-diol.

9. The composition of claim 1 wherein the complexing agent is selected from the group consisting of organic acids and their salts, amino acetic acids, amino acids, carboxylic acids, polyamines, ammonia based compounds, quaternary ammonium compounds, inorganic acids, compounds with both carboxylic and amino functions, ethylenediaminetetraacetic acid, diethylene triamine pentaacetic acid, and any mixtures thereof.

10. The composition of claim 9 wherein the complexing agent is selected from amino acids.

11. The composition of claim 10 wherein the complexing agent is glycine.

12. The composition of claim 1 further comprising an oxidizer.

13. A composition comprising:

a) 0.1 wt % to about 10 wt % of an abrasive;

b) 0.01 wt% to about 0.1 wt % of a first surfactant comprising a phosphate;

c) 0.01 wt% to about 0.1 wt % of a second surfactant comprising an acetylenic compound;

d) 1 wt % to about 20 wt% of a complexing agent;

e) 0.01 wt % to about 5 wt% of at least one azole; and

f) water.

14. A composition comprising:

a) 0.01 wt % to about 1.0 wt % of an abrasive;

b) 0.001 wt% to about 0.01 wt % of a first surfactant comprising a phosphate;

c) 0.001 wt% to about 0.01 wt % of a second surfactant comprising an acetylenic compound;

d) 0.1 wt % to about 2.0 wt% of a complexing agent;

e) 0.001 wt % to 0.5 wt% of at least one azole;

f) 0.1 wt % to about 5 wt % oxidizer; and

g) water.

15. A method of removing a copper layer from a substrate, comprising contacting the copper layer with the composition of claim 14, wherein the composition removes the copper layer at a rate that is at least 75 percent of a peak removal rate of the composition.

16. A method of polishing a substrate, comprising the steps of:

(a) providing a substrate with at least one metal layer;

(b) contacting the substrate with a composition of claim 14, and

(c) chemically mechanically polishing the substrate with the composition.